



EMB-1000-U

Datasheet Version 1.0

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1. Overview

EMB-1000-U is a powerful, generic Wi-Fi+BT+BLE MCU modules that targets a wide variety of applications, ranging from low-power sensor networks to the most demanding tasks, such as voice encoding, music streaming and MP3 decoding.

At the core of the two modules are the ESP32-D0WD chip*. The chip embedded is designed to be scalable and adaptive. There are two CPU cores that can be individually controlled, and the CPU clock frequency is 240 MHz. The user may also power off the CPU and make use of the low-power co-processor to constantly monitor the peripherals for changes or crossing of thresholds. ESP32 integrates a rich set of peripherals, ranging from capacitive touch sensors, Hall sensors, SD card interface, Ethernet, high-speed SPI, UART, I²S and I²C.

Note:

* For details on the part numbers of the ESP32 family of chips, please refer to the document [ESP32 Datasheet](#).

The integration of Bluetooth, Bluetooth LE and Wi-Fi ensures that a wide range of applications can be targeted, and that the module is all-around: using Wi-Fi allows a large physical range and direct connection to the internet through a Wi-Fi router, while using Bluetooth allows the user to conveniently connect to the phone or broadcast low energy beacons for its detection. The sleep current of the ESP32 chip is less than 5 μ A, making it suitable for battery powered and wearable electronics applications. The module supports a data rate of up to 150 Mbps, and output power at the antenna to ensure the widest physical range. As such the module does offer industry-leading specifications and the best performance for electronic integration, range, power consumption, and connectivity.

The operating system chosen for ESP32 is free RTOS with LwIP; TLS 1.2 with hardware acceleration is built in as well. Secure (encrypted) over the air (OTA) upgrade is also supported, so that developers can upgrade their products even after their release, at minimum cost and effort.

The antenna supported on EMB-1000-U has the following specifications:

- Electrical Properties
 - Frequency range: 2.4 GHz ~ 2.5 GHz
 - Impedance: 50 Ω
 - Return loss: -10 dB or less
 - Peak gain: 2.33 dBi
 - Cable: Ø1.13 Normal

- Physical Properties
 - Antenna body: PCB
 - Operating temperature: - 40°C ~ + 85°C

Table 1 provides the specifications of EMB-1000-U.

Table 1: EMB-1000-U Specifications

Categories	Items	Specifications
Certification	RF Certification	FCC/IC
	Green Certification	REACH/RoHS
Test	Reliability	HTOL/HTSL/uHAST/TCT/ESD
Wi-Fi	Protocols	802.11 b/g/n (802.11n up to 150 Mbps) A-MPDU and A-MSDU aggregation and 0.4 μ s guard interval support
	Frequency range	2.4 ~ 2.5 GHz
Bluetooth	Protocols	Bluetooth v4.2 BR/EDR and BLE specification
	Radio	NZIF receiver with -97 dBm sensitivity
		class-2 transmitter
		AFH
Audio	CVSD and SBC	
Hardware	Module interfaces	SD card, UART, SPI, SDIO, I ² C, LED PWM, Motor PWM, I ² S, IR, pulse counter, GPIO, capacitive touch sensor, ADC, DAC
	On-chip sensor	Hall sensor
	On-board clock	40 MHz crystal
	Operating voltage/Power supply	2.7 ~ 3.6V
	Operating current	Average: 80 mA
	Minimum current delivered by power supply	500 mA
	Recommended operating temperature range	-10°C ~ +60°C

2. Pin Definitions

2.1 Pin Layout

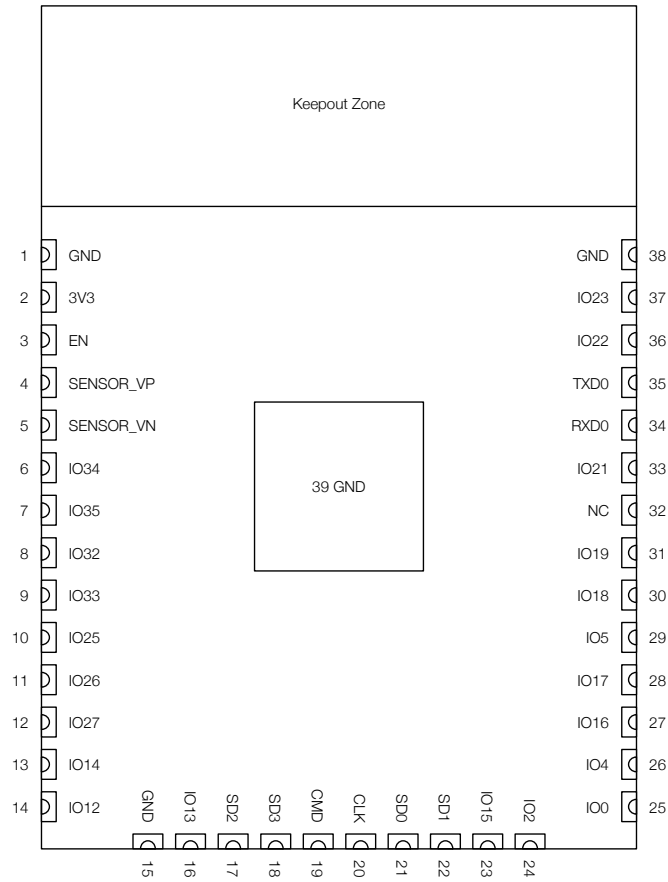


Figure 2: EMB-1000-U Pin Layout (Top View)

2.2 Pin Description

EMB-1000-U has 38 pins. See pin definitions in Table 2.

Table 2: Pin Definitions

Name	No.	Type	Function
GND	1	P	Ground
3V3	2	P	Power supply
EN	3	I	Module-enable signal. Active high.
SENSOR_VP	4	I	GPIO36, ADC1_CH0, RTC_GPIO0
SENSOR_VN	5	I	GPIO39, ADC1_CH3, RTC_GPIO3
IO34	6	I	GPIO34, ADC1_CH6, RTC_GPIO4
IO35	7	I	GPIO35, ADC1_CH7, RTC_GPIO5
IO32	8	I/O	GPIO32, XTAL_32K_P (32.768 kHz crystal oscillator input), ADC1_CH4, TOUCH9, RTC_GPIO9
IO33	9	I/O	GPIO33, XTAL_32K_N (32.768 kHz crystal oscillator output), ADC1_CH5, TOUCH8, RTC_GPIO8

Name	No.	Type	Function
IO25	10	I/O	GPIO25, DAC_1, ADC2_CH8, RTC_GPIO6, EMAC_RXD0
IO26	11	I/O	GPIO26, DAC_2, ADC2_CH9, RTC_GPIO7, EMAC_RXD1
IO27	12	I/O	GPIO27, ADC2_CH7, TOUCH7, RTC_GPIO17, EMAC_RX_DV
IO14	13	I/O	GPIO14, ADC2_CH6, TOUCH6, RTC_GPIO16, MTMS, HSPICLK, HS2_CLK, SD_CLK, EMAC_TXD2
IO12	14	I/O	GPIO12, ADC2_CH5, TOUCH5, RTC_GPIO15, MTDI, HSPIQ, HS2_DATA2, SD_DATA2, EMAC_TXD3
GND	15	P	Ground
IO13	16	I/O	GPIO13, ADC2_CH4, TOUCH4, RTC_GPIO14, MTCK, HSPID, HS2_DATA3, SD_DATA3, EMAC_RX_ER
SHD/SD2*	17	I/O	GPIO9, SD_DATA2, SPIHD, HS1_DATA2, U1RXD
SWP/SD3*	18	I/O	GPIO10, SD_DATA3, SPIWP, HS1_DATA3, U1TXD
SCS/CMD*	19	I/O	GPIO11, SD_CMD, SPICS0, HS1_CMD, U1RTS
SCK/CLK*	20	I/O	GPIO6, SD_CLK, SPICLK, HS1_CLK, U1CTS
SDO/SD0*	21	I/O	GPIO7, SD_DATA0, SPIQ, HS1_DATA0, U2RTS
SDI/SD1*	22	I/O	GPIO8, SD_DATA1, SPID, HS1_DATA1, U2CTS
IO15	23	I/O	GPIO15, ADC2_CH3, TOUCH3, MTDO, HSPICS0, RTC_GPIO13, HS2_CMD, SD_CMD, EMAC_RXD3
IO2	24	I/O	GPIO2, ADC2_CH2, TOUCH2, RTC_GPIO12, HSPIWP, HS2_DATA0, SD_DATA0
IO0	25	I/O	GPIO0, ADC2_CH1, TOUCH1, RTC_GPIO11, CLK_OUT1, EMAC_TX_CLK
IO4	26	I/O	GPIO4, ADC2_CH0, TOUCH0, RTC_GPIO10, HSPIHD, HS2_DATA1, SD_DATA1, EMAC_TX_ER
IO16	27	I/O	GPIO16, HS1_DATA4, U2RXD, EMAC_CLK_OUT
IO17	28	I/O	GPIO17, HS1_DATA5, U2TXD, EMAC_CLK_OUT_180
IO5	29	I/O	GPIO5, VSPICS0, HS1_DATA6, EMAC_RX_CLK
IO18	30	I/O	GPIO18, VSPICLK, HS1_DATA7
IO19	31	I/O	GPIO19, VSPIQ, U0CTS, EMAC_TXD0
NC	32	-	-
IO21	33	I/O	GPIO21, VSPIHD, EMAC_TX_EN
RXD0	34	I/O	GPIO3, U0RXD, CLK_OUT2
TXD0	35	I/O	GPIO1, U0TXD, CLK_OUT3, EMAC_RXD2
IO22	36	I/O	GPIO22, VSPIWP, U0RTS, EMAC_TXD1
IO23	37	I/O	GPIO23, VSPID, HS1_STROBE
GND	38	P	Ground

Notice:

* Pins SCK/CLK, SDO/SD0, SDI/SD1, SHD/SD2, SWP/SD3 and SCS/CMD, namely, GPIO6 to GPIO11 are connected to the integrated SPI flash integrated on the module and are not recommended for other uses.

2.3 Strapping Pins

ESP32 has five strapping pins, which can be seen in Chapter 6 Schematics:

- MTDI
- GPIO0
- GPIO2
- MTDO
- GPIO5

Software can read the values of these five bits from register "GPIO_STRAPPING".

During the chip's system reset (power-on-reset, RTC watchdog reset and brownout reset), the latches of the strapping pins sample the voltage level as strapping bits of "0" or "1", and hold these bits until the chip is powered down or shut down. The strapping bits configure the device's boot mode, the operating voltage of VDD_SDIO and other initial system settings.

Each strapping pin is connected to its internal pull-up/pull-down during the chip reset. Consequently, if a strapping pin is unconnected or the connected external circuit is high-impedance, the internal weak pull-up/pull-down will determine the default input level of the strapping pins.

To change the strapping bit values, users can apply the external pull-down/pull-up resistances, or use the host MCU's GPIOs to control the voltage level of these pins when powering on ESP32.

After reset, the strapping pins work as normal-function pins.

Refer to Table 3 for a detailed boot-mode configuration by strapping pins.

Table 3: Strapping Pins

Voltage of Internal LDO (VDD_SDIO)					
Pin	Default	3.3V		1.8V	
MTDI	Pull-down	0		1	
Bootling Mode					
Pin	Default	SPI Boot		Download Boot	
GPIO0	Pull-up	1		0	
GPIO2	Pull-down	Don't-care		0	
Enabling/Disabling Debugging Log Print over U0TXD During Bootling					
Pin	Default	U0TXD Active		U0TXD Silent	
MTDO	Pull-up	1		0	
Timing of SDIO Slave					
Pin	Default	Falling-edge Input Falling-edge Output	Falling-edge Input Rising-edge Output	Rising-edge Input Falling-edge Output	Rising-edge Input Rising-edge Output
MTDO	Pull-up	0	0	1	1
GPIO5	Pull-up	0	1	0	1

Note:

- Firmware can configure register bits to change the settings of "Voltage of Internal LDO (VDD_SDIO)" and "Timing of SDIO Slave" after bootling.
- EMB-1000-U integrates a 3.3V SPI flash, so the pin MTDI cannot be set to 1 when the modules are powered up.

3. Functional Description

This chapter describes the modules and functions integrated in EMB-1000-U.

3.1 CPU and Internal Memory

ESP32-D0WD contains a dual-core Xtensa® 32-bit LX6 MCU. The internal memory includes:

- 448 KB of ROM for booting and core functions.
- 520 KB of on-chip SRAM for data and instructions.
- 8 KB of SRAM in RTC, which is called RTC FAST Memory and can be used for data storage; it is accessed by the main CPU during RTC Boot from the Deep-sleep mode.
- 8 KB of SRAM in RTC, which is called RTC SLOW Memory and can be accessed by the co-processor during the Deep-sleep mode.
- 1 Kbit of eFuse: 256 bits are used for the system (MAC address and chip configuration) and the remaining 768 bits are reserved for customer applications, including flash-encryption and chip-ID.

3.2 External Flash and SRAM

ESP32 supports multiple external QSPI flash and SRAM chips. More details can be found in Chapter SPI in the [ESP32 Technical Reference Manual](#). ESP32 also supports hardware encryption/decryption based on AES to protect developers' programs and data in flash.

ESP32 can access the external QSPI flash and SRAM through high-speed caches.

- The external flash can be mapped into CPU instruction memory space and read-only memory space simultaneously.
 - When external flash is mapped into CPU instruction memory space, up to 11 MB+248 KB can be mapped at a time. Note that if more than 3 MB+248 KB are mapped, cache performance will be reduced due to speculative reads by the CPU.
 - When external flash is mapped into read-only data memory space, up to 4 MB can be mapped at a time. 8-bit, 16-bit and 32-bit reads are supported.
- External SRAM can be mapped into CPU data memory space. Up to 4 MB can be mapped at a time. 8-bit, 16-bit and 32-bit reads and writes are supported.

EMB-1000-U integrates a 4 MB of external SPI flash. The integrated SPI flash is connected to GPIO6, GPIO7, GPIO8, GPIO9, GPIO10 and GPIO11. These six pins cannot be used as regular GPIOs.

3.3 Crystal Oscillators

The module uses a 40-MHz crystal oscillator.

3.4 RTC and Low-Power Management

With the use of advanced power-management technologies, ESP32 can switch between different power modes.

For details on ESP32's power consumption in different power modes, please refer to section "RTC and Low-Power Management" in [ESP32 Datasheet](#).

4. Peripherals and Sensors

Please refer to Section Peripherals and Sensors in [ESP32 Datasheet](#).

Note:

External connections can be made to any GPIO except for GPIOs in the range 6-11. These six GPIOs are connected to the module's integrated SPI flash. For details, please see Section 6 Schematics.

5. Electrical Characteristics

5.1 Absolute Maximum Ratings

Stresses beyond the absolute maximum ratings listed in the table below may cause permanent damage to the device. These are stress ratings only, and do not refer to the functional operation of the device.

Table 4: Absolute Maximum Ratings

Symbol	Parameter	Min	Max	Unit
VDD33	Power supply voltage	-0.3	3.6	V
T_{store}	Storage temperature	-40	150	°C

5.2 Recommended Operating Conditions

Table 5: Recommended Operating Conditions

Symbol	Parameter	Min	Typical	Max	Unit
VDD33	Power supply voltage	2.7	3.3	3.6	V
I_{VDD}	Current delivered by external power supply	0.5	-	-	A
T	Operating temperature	-40	-	85	°C

5.3 DC Characteristics (3.3V, 25°C)

Table 6: DC Characteristics

Symbol	Parameter	Min	Typ	Max	Unit
C_{IN}	Pin capacitance	-	2	-	pF
V_{IH}	High-level input voltage	$0.75 \times VDD^1$	-	$VDD + 0.3$	V
V_{IL}	Low-level input voltage	-0.3	-	$0.25 \times VDD$	V
I_{IH}	High-level input current	-	-	50	nA
I_{IL}	Low-level input current	-	-	50	nA
V_{OH}	High-level output voltage	$0.8 \times VDD$	-	-	V
V_{OL}	Low-level output voltage	-	-	$0.1 \times VDD$	V
I_{OH}	High-level source current (VDD = 3.3V, V_{OH} = 2.64V, PAD_DRIVER = 3)	-	40	-	mA
I_{OL}	Low-level sink current (VDD = 3.3V, V_{OL} = 0.495V, PAD_DRIVER = 3)	-	28	-	mA
R_{PU}	Pull-up resistor	-	45	-	k Ω
R_{PD}	Pull-down resistor	-	45	-	k Ω
V_{IL_nRST}	Low-level input voltage of EN to reset the module	-	-	0.6	V

1. VDD is the I/O voltage for a particular power domain of pins. More details can be found in Appendix IO_MUX of [ESP32 Datasheet](#).

5.4 Wi-Fi Radio

Table 7: Wi-Fi Radio Characteristics

Parameter	Condition	Min	Typical	Max	Unit
Input frequency	-	2412	-	2462	MHz
Output impedance*	-	-	*	-	Ω
Sensitivity Adjacent channel rejection	11b, 1 Mbps	-	-98	-	dBm
	11b, 11 Mbps	-	-89	-	dBm
	11g, 6 Mbps	-	-92	-	dBm
	11g, 54 Mbps	-	-74	-	dBm
	11n, HT20, MCS0	-	-91	-	dBm
	11n, HT20, MCS7	-	-71	-	dBm
	11n, HT40, MCS0	-	-89	-	dBm
	11n, HT40, MCS7	-	-69	-	dBm

*For the modules that use IPEX antennas, the output impedance is 50Ω . For other modules without IPEX antennas, users do not need to concern about the output impedance.

5.5 BLE Radio

5.5.1 Receiver

Table 8: Receiver Characteristics – BLE

Parameter	Conditions	Min	Typ	Max	Unit
Sensitivity @30.8% PER	-	-	-97	-	dBm
Maximum received signal @30.8% PER	-	0	-	-	dBm
Co-channel C/I	-	-	+10	-	dB
Adjacent channel selectivity C/I	$F = F_0 + 1 \text{ MHz}$	-	-5	-	dB
	$F = F_0 - 1 \text{ MHz}$	-	-5	-	dB
	$F = F_0 + 2 \text{ MHz}$	-	-25	-	dB
	$F = F_0 - 2 \text{ MHz}$	-	-35	-	dB
	$F = F_0 + 3 \text{ MHz}$	-	-25	-	dB
	$F = F_0 - 3 \text{ MHz}$	-	-45	-	dB
Out-of-band blocking performance	30 MHz ~ 2000 MHz	-10	-	-	dBm
	2000 MHz ~ 2400 MHz	-27	-	-	dBm
	2500 MHz ~ 3000 MHz	-27	-	-	dBm
	3000 MHz ~ 12.5 GHz	-10	-	-	dBm
Intermodulation	-	-36	-	-	dBm

5.5.2 Transmitter

Table 9: Transmitter Characteristics – BLE

Parameter	Conditions	Min	Typ	Max	Unit
Adjacent channel transmit power	$F = F_0 \pm 2 \text{ MHz}$	-	-52	-	dBm
	$F = F_0 \pm 3 \text{ MHz}$	-	-58	-	dBm
	$F = F_0 \pm > 3 \text{ MHz}$	-	-60	-	dBm
$\Delta f_{1\text{avg}}$	-	-	-	265	kHz
$\Delta f_{2\text{max}}$	-	247	-	-	kHz
$\Delta f_{2\text{avg}}/\Delta f_{1\text{avg}}$	-	-	-0.92	-	-
ICFT	-	-	-10	-	kHz
Drift rate	-	-	0.7	-	kHz/50 μs
Drift	-	-	2	-	kHz

5.6 Reflow Profile

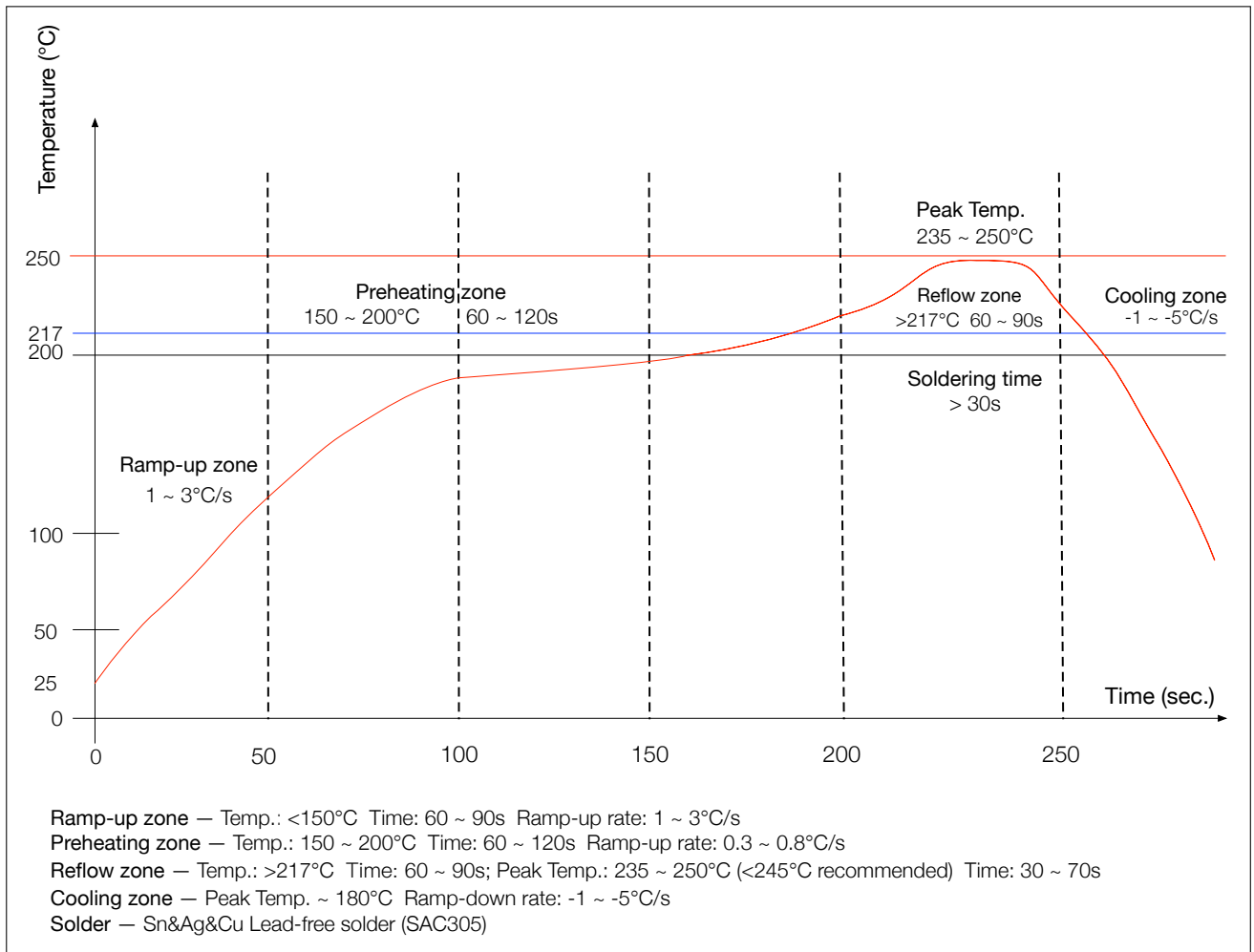


Figure 3: Reflow Profile

6. Schematics

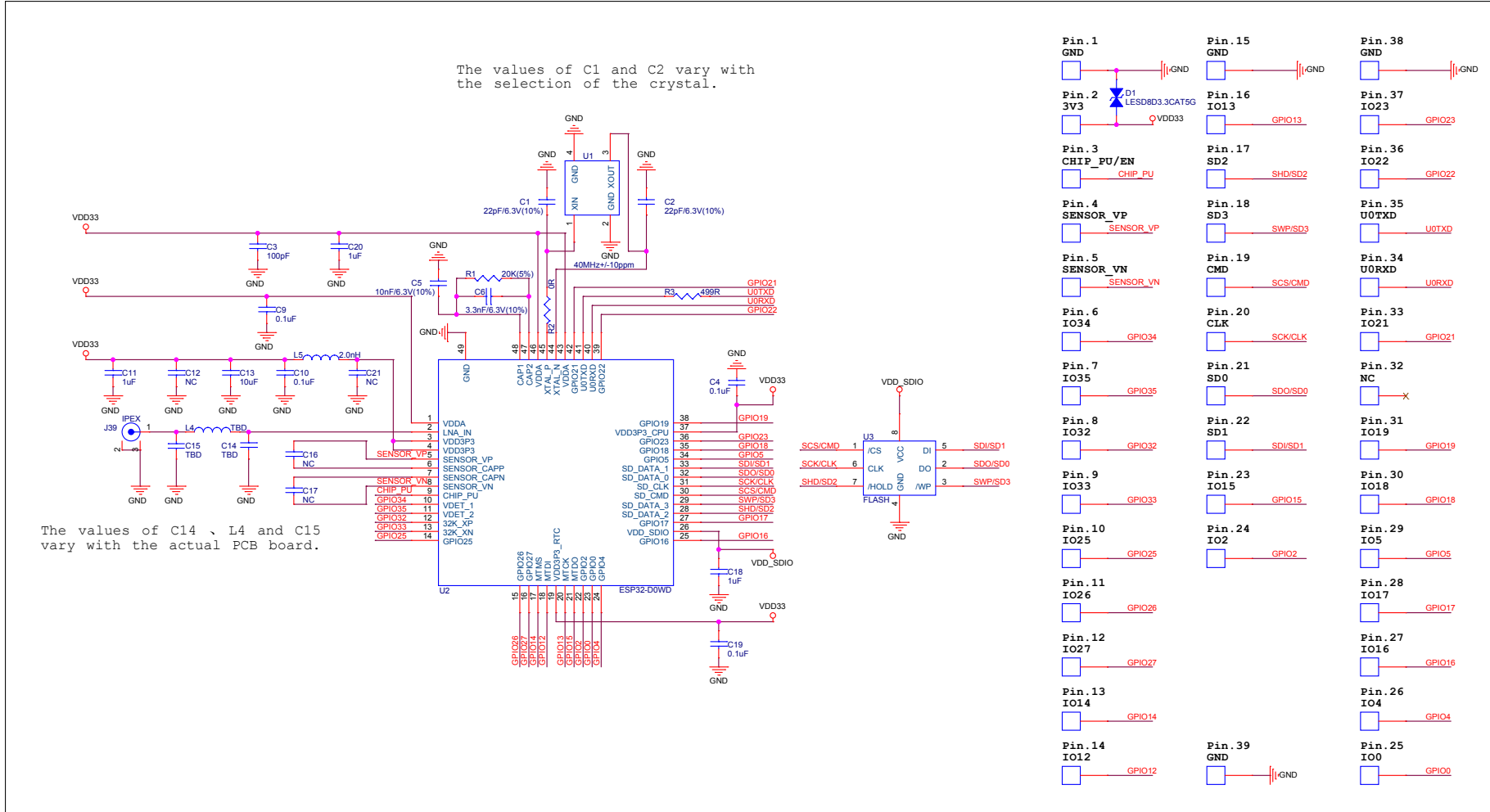


Figure 4: EMB-1000-U Schematics

7. Peripheral Schematics

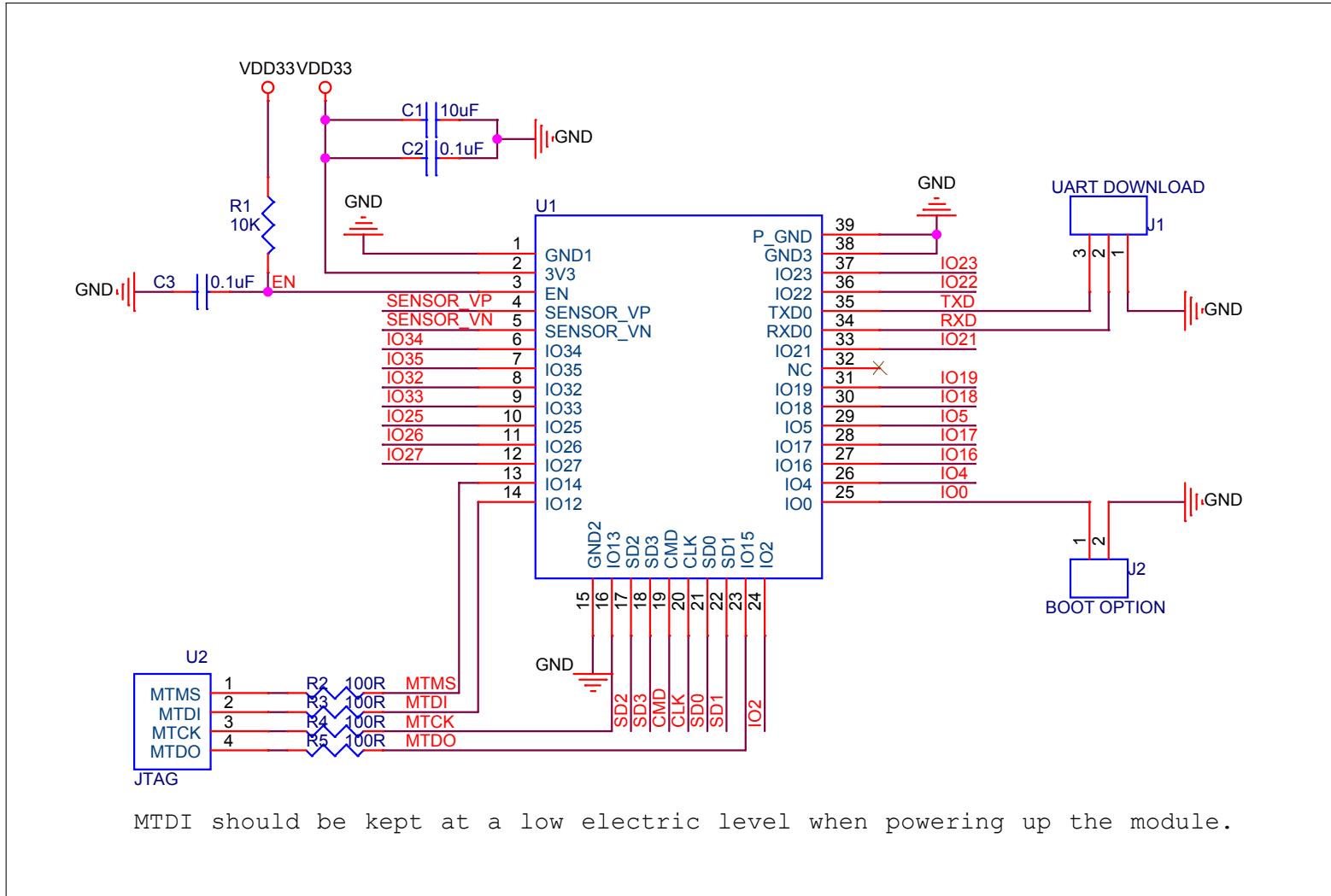


Figure 5: EMB-1000-U Peripheral Schematics

8. Physical Dimensions

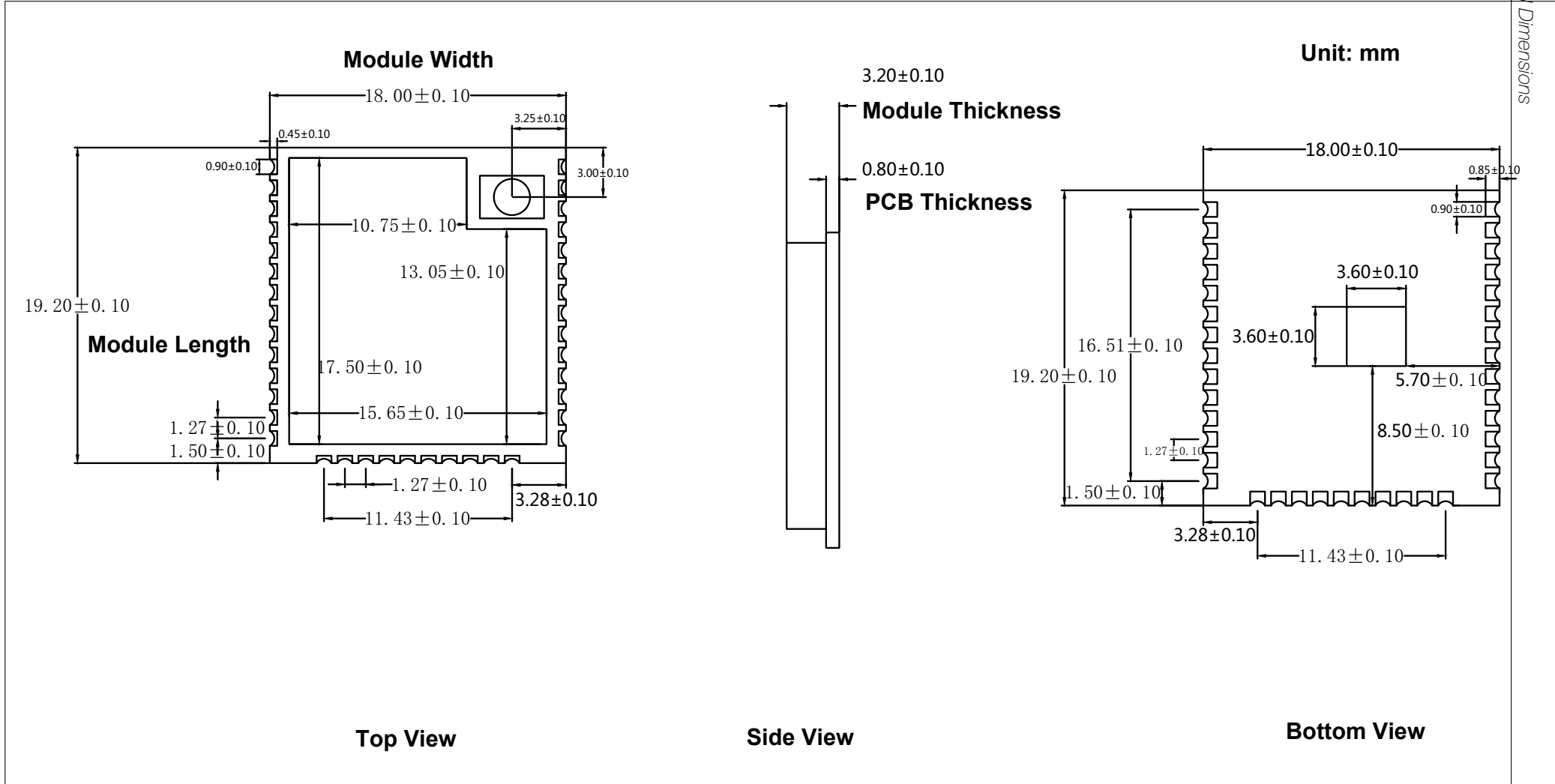


Figure 6: Physical Dimensions of EMB-1000-U

Revision History

Date	Version	Release notes
2018.08	V1.0	First release.

FCC Statement

This equipment complies with FCC radiation exposure limits set forth for an uncontrolled environment. This equipment should be installed and operated with minimum distance 20cm between the radiator & your body.

This transmitter must not be co-located or operating in conjunction with any other antenna or transmitter.

Le rayonnement de la classe b respecte ISSED fixaient un environnement non contrôlés. Installation et mise en œuvre de ce matériel devrait avec échangeur distance minimale entre 20 cm ton corps. Lanceurs ou ne peuvent pas coexister cette antenne ou capteurs avec d'autres.

FCC Radiation Exposure Statement:

This equipment complies with FCC radiation exposure limits set forth for an uncontrolled environment. This equipment should be installed and operated with minimum distance 20cm between the radiator & your body.

ISED RSS Warning/ISED RF Exposure Statement

ISED RSS Warning:

This device complies with Innovation, Science and Economic Development Canada licence-exempt RSS standard(s). Operation is subject to the following two conditions: (1) this device may not cause interference, and (2) this device must accept any interference, including interference that may cause undesired operation of the device.

Le présent appareil est conforme aux CNR d'ISED applicables aux appareils radio exempts de licence. L'exploitation est autorisée aux deux conditions suivantes:

- (1) l'appareil ne doit pas produire de brouillage, et
- (2) l'utilisateur de l'appareil doit accepter tout brouillage radioélectrique subi, même si le brouillage est susceptible d'en compromettre le fonctionnement.

ISED RF exposure statement:

This equipment complies with ISSED radiation exposure limits set forth for an uncontrolled environment. This equipment should be installed and operated with minimum distance 20cm between the radiator & your body. This transmitter must not be co-located or operating in conjunction with any other antenna or transmitter.

Le rayonnement de la classe b respecte ISSED fixaient un environnement non contrôlés. Installation et mise en œuvre de ce matériel devrait avec échangeur distance minimale entre 20 cm ton corps. Lanceurs ou ne peuvent pas coexister cette antenne ou capteurs avec d'autres.

FCC & ISSED Label Instructions

"2000012AME8EMB1KU,IC:24134-EMB1KU" or "Contains
 "FCC ID:2AME8EMB1KU,IC:24134-EMB1KU" Any similar wording that expresses the same meaning may be used.